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Substitute for form 1449A/PTO	Application Number	10/634,662
OCT 2.7 2005 p.:	Filing Date	August 4, 2003
SUPPLEMENTAL INFORMATION	First Named Inventor	Chang, et al.
DISCLOSURE STATEMENT	Group Art Unit	1762
APPLICANT	Examiner Name	Wesley D. Markham
(Use as many sheets as necessary)	Attorney Docket Number	APPM/005975.P1/CPI/COPPER/LB/PJS

Submission Date

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A1	US 6790773	09/	14/2004	Drewery, et al.						
A2	US 20050081882	04/	21/2005	Greer, et al.						
А3	US-20050006799	01/	13/2005	Gregg, et al.						
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B1	WO 2005/020317		03/03/2005	Chang, et al.						
B2	EP 1 293 509		.09/10/2002	Kawano, et al.						
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C1	International Search R (APPM/005975PC03)	International Search Report dated July 29, 2005 regarding International Application No. PCT/US2005/010203 (APPM/005975PC03)								
C2	Ruthenium," Chemical	Aspects of	Electronic Cerai	mics Processing, Symposi	rom Bis(2, 4- ium Mater. R	dimethylpentadienyl) es. Soc., Warrendale,				
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Examiner /Kelly Stouffer/ Date Considered 09/20/2006

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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form sudgestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

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May 23, 2005

Under the Panerwork Reduction Act of 1995, no persons are required information unless it displays a valid OMB control number. 10/634,662 titute for form 1449A/PTO Application Number Filing Date August 4, 2003 SEPPLEMENTAL INFORMATION First Named Inventor Chang, et al. SCLOSURE STATEMENT BY 1762 Group Art Unit **APPLICANT Examiner Name** Wesley D. Markham

Attorney Docket Number

Submission Date

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Examiner /Kelly Stouffer/ Date Considered 09/20/2006

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U.S. Patent and Tradamark Office: U.S. DEPARTMENT OF COMMERCE the Paperwork Reduction Act of 1995, no persons are required t mation unless it displays a valid OMB control number. A 运) Substitute for form 1449A/PTO

Attorney Docket Number

SUPPLEMENTAL INFORMATION **DISCLOSURE STATEMENT BY APPLICANT**

10/634,662 **Application Number** Filing Date August 4, 2003 First Named Inventor Chang, et al. **Group Art Unit** 1762 **Examiner Name** Unknown

(Use as many sheets as necessary)

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AMAT/5975.P1/CPI/COPPER/LB/PJS Submission Date September 20, 2004

				U.S. PATENT	DOCUMENTS				
Examiner Initials*	Cite No.		Document Number	Publication Date	Pages, Columns, Lines				
iniuais	No.		Number-Kind Code ^{2 (I known)}	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Relevant Passages or I Figures Appear			
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A2 US-6,605,735 B2				08/12/2003	Kawano, et al.				
	А3	US	6-6,479,100 B2	11/12/2002	Jin, et al.				
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$\overline{\mathbf{A}}$	A6	US	S-2001/0006838 A1	07/05/2001	Won, et al.				
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/Kelly Stouffer/ 09/20/2006 **Date Considered**

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered, include copy of this form with next communication to applicant's unique citation designation number (optional). Is see Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached.

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A	A6	6,527,855	03/04/03	DelaRosa, et al.	117	89	10/10/01	١.		
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